



PJM3404NSA

N-Channel Enhancement Mode Power MOSFET

Product Summary

- $V_{DS} = 30V, I_D = 5A$
- $R_{DS(on)} < 31m\Omega @ V_{GS} = 10V$
- $R_{DS(on)} < 40m\Omega @ V_{GS} = 4.5V$

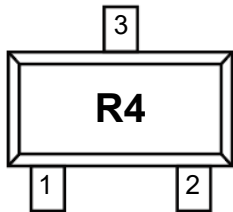
Features

- Advanced Trench Technology
- RoHS and Reach Compliant
- Halogen and Antimony Free
- Moisture Sensitivity Level 1

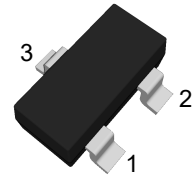
Application

- Load Switch
- PWM Application
- Power Management

Marking Code



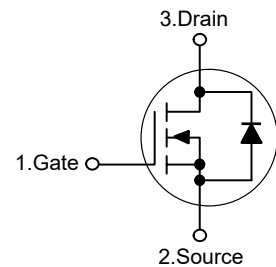
SOT-23



(Top View)

Pin	Description
1	Gate
2	Source
3	Drain

Schematic Diagram



Absolute Maximum Ratings

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	5	A
Drain Current-Pulsed ^{Note1}	I_{DM}	16	A
Maximum Power Dissipation	P_D	1.2	W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

Thermal Characteristics

Thermal Resistance, Junction-to-Ambient ^{Note2}	$R_{\theta JA}$	104	°C/W
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Electrical Characteristics

(Ta=25°C unless otherwise specified)

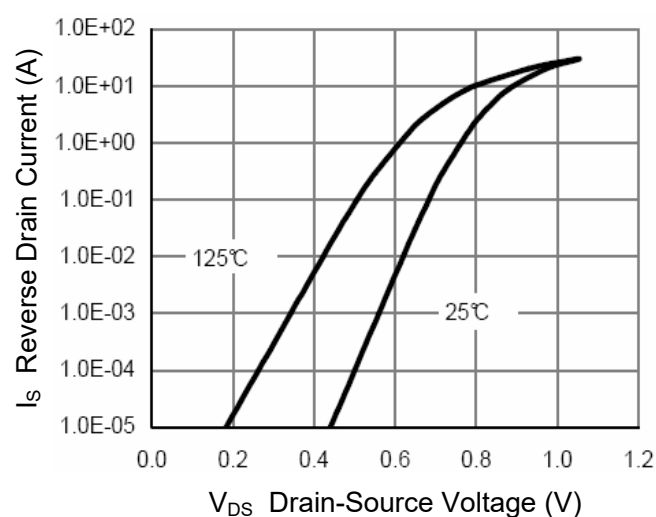
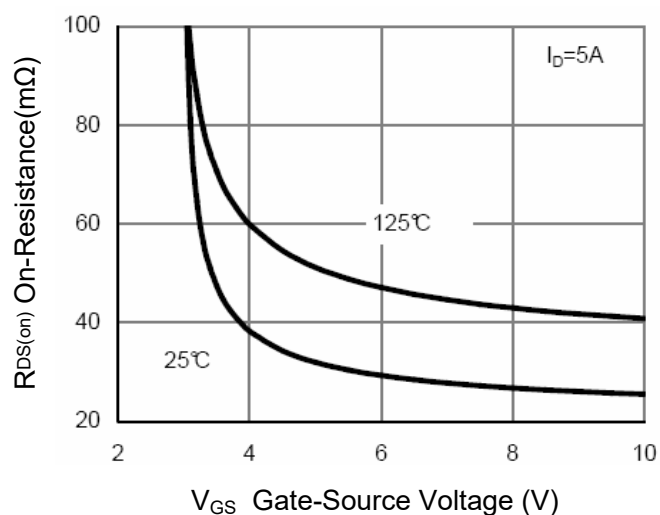
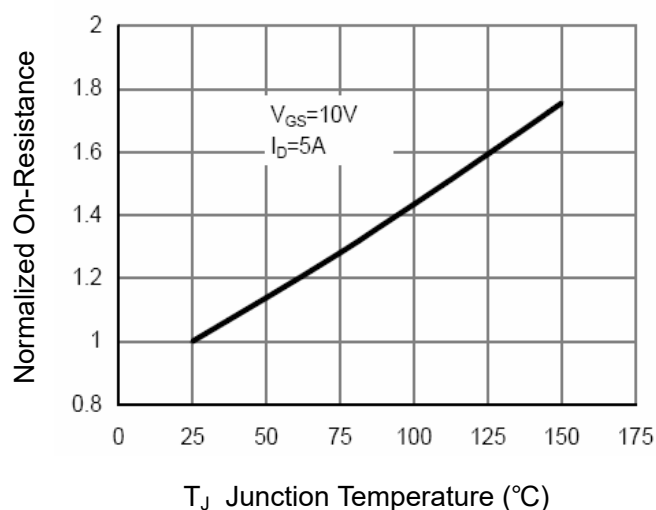
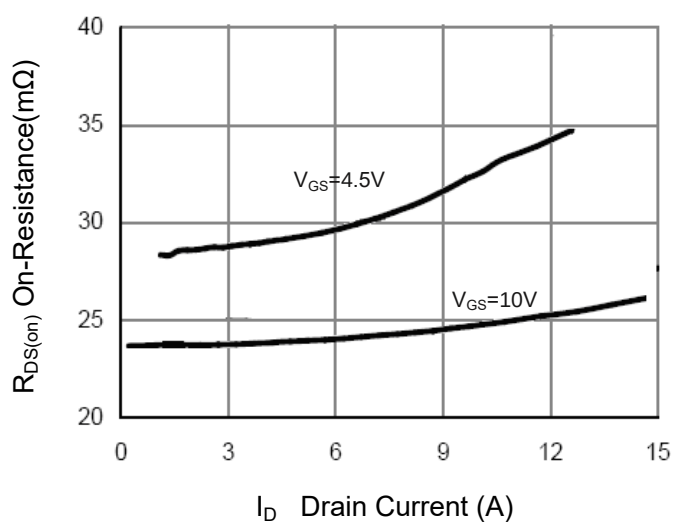
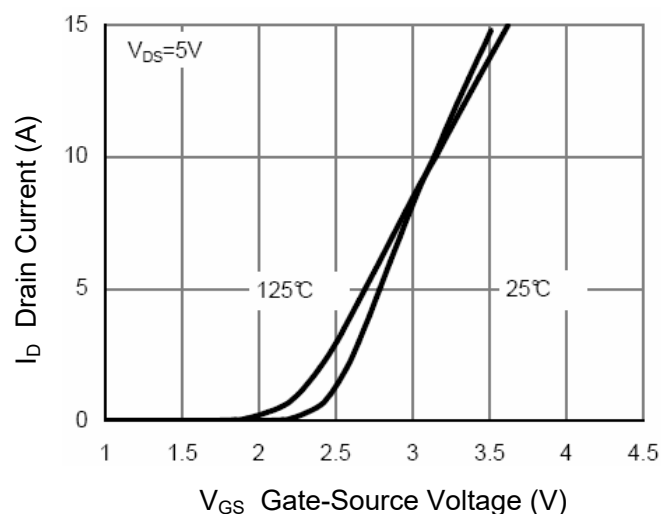
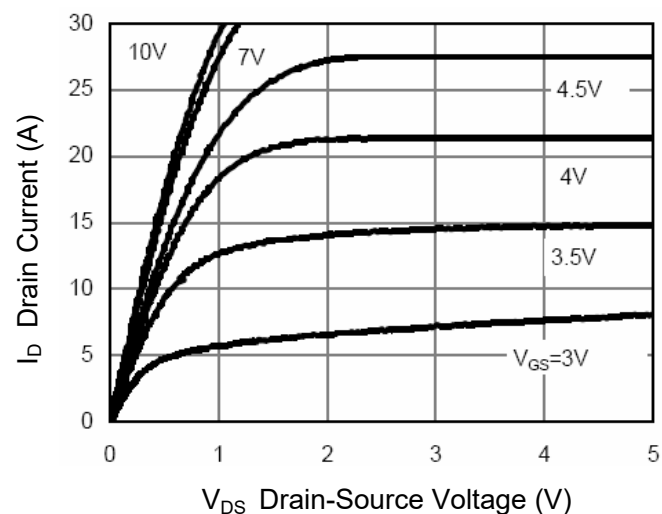
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V,I _D =250μA	30	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	--	--	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V,V _{DS} =0V	--	--	±100	nA
Gate Threshold Voltage ^{Note3}	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	1.2	1.5	2.4	V
Drain-Source On-Resistance ^{Note3}	R _{DS(on)}	V _{GS} =10V,I _D =5A	--	22	31	mΩ
		V _{GS} =4.5V,I _D =5A	--	28	40	mΩ
Forward Transconductance ^{Note3}	g _{FS}	V _{DS} =5V,I _D =1A	--	3	--	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =15V,V _{GS} =0V,f=1MHz	--	351	--	pF
Output Capacitance	C _{oss}		--	58	--	pF
Reverse Transfer Capacitance	C _{rss}		--	13	--	pF
Gate Resistance	R _G	V _{DS} =0V,V _{GS} =0V,f=1MHz	--	23	--	Ω
Total Gate Charge	Q _g	V _{DS} =15V,I _D =5A, V _{GS} =10V	--	12.6	--	nC
Gate-Source Charge	Q _{gs}		--	1.9	--	nC
Gate-Drain Charge	Q _{gd}		--	2.6	--	nC
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, R _L =3Ω V _{GS} =10V,R _{GEN} =3Ω	--	5	--	nS
Turn-on Rise Time	t _r		--	3	--	nS
Turn-off Delay Time	t _{d(off)}		--	15	--	nS
Turn-off Fall Time	t _f		--	3.5	--	nS
Source-Drain Diode Characteristics						
Diode Forward Voltage ^{Note3}	V _{SD}	V _{GS} =0V,I _S =5A	--	--	1.2	V
Diode Forward Current ^{Note2}	I _S		--	--	5	A

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \leq 10$ sec.

3. Pulse Test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

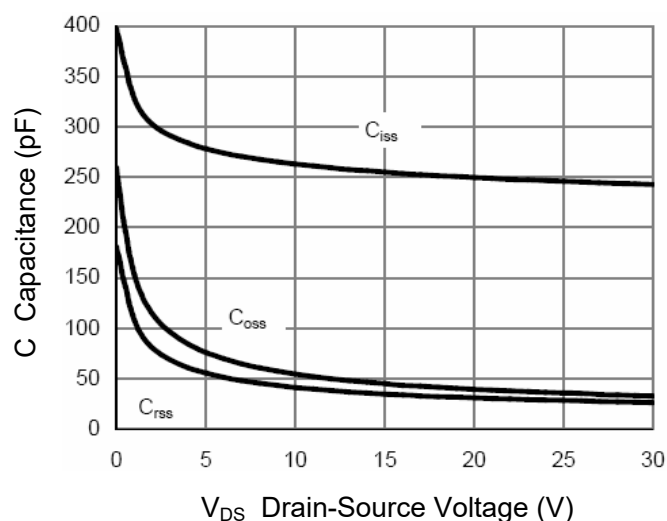
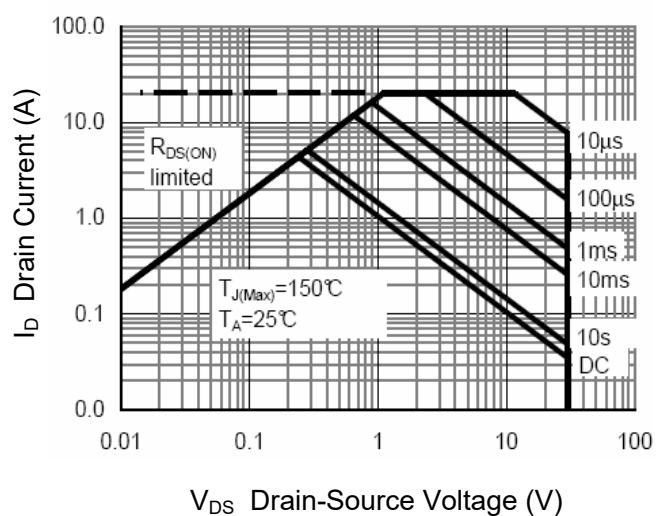
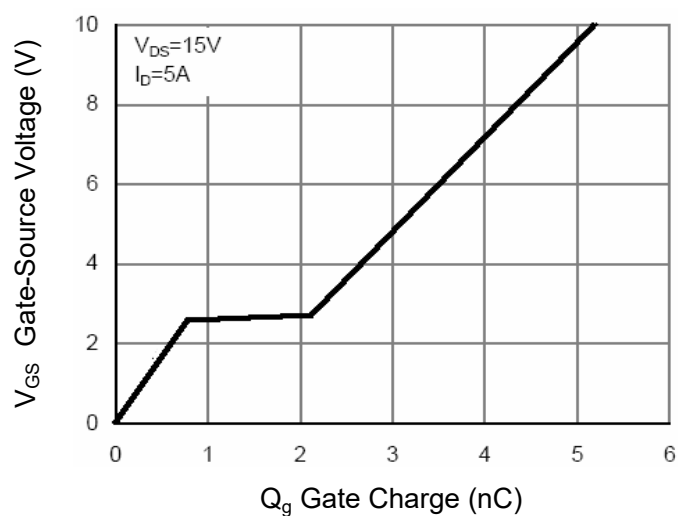
Typical Characteristic Curves





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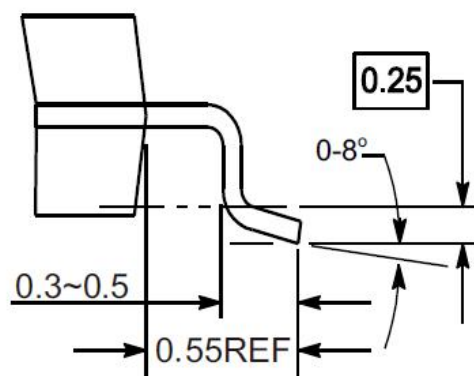
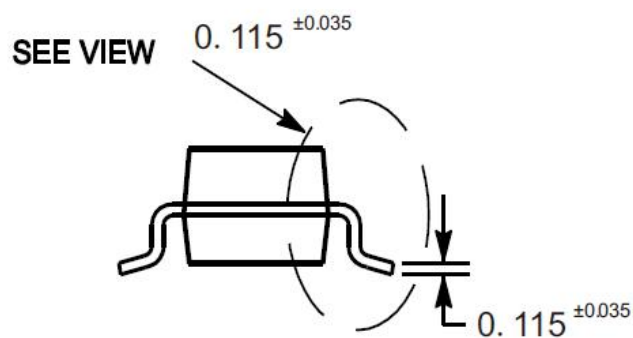
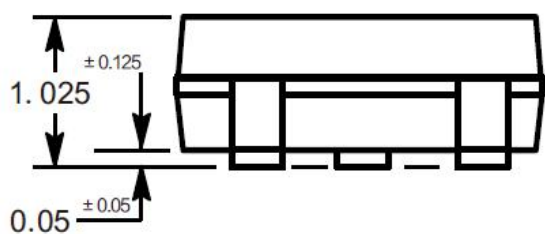
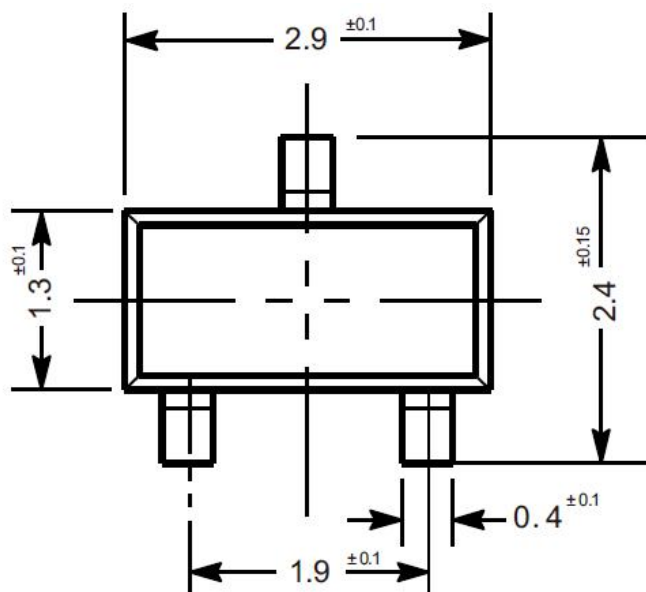
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Package Outline

SOT-23

Dimensions in mm



VIEW C

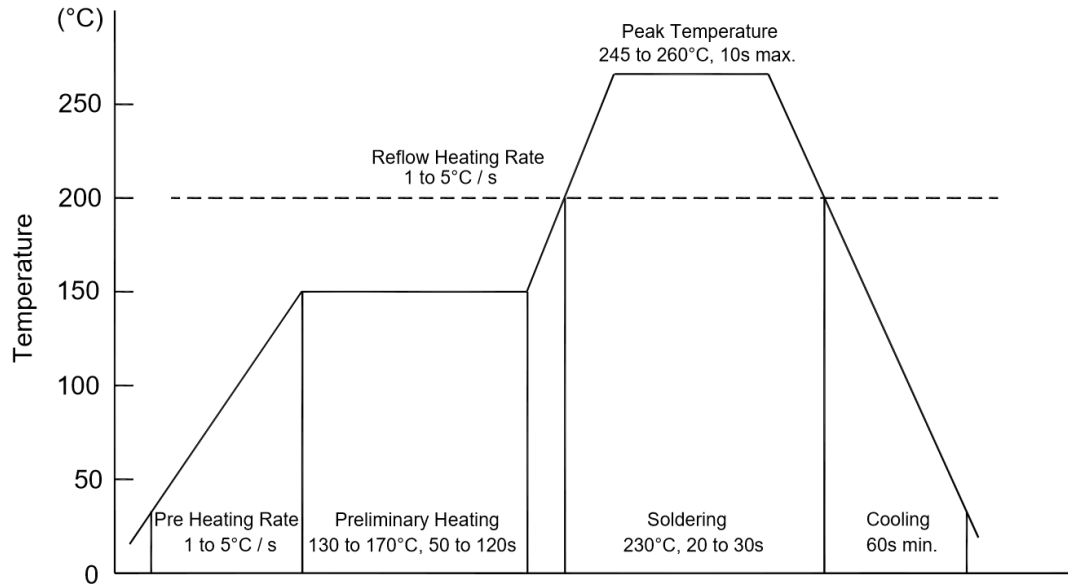
Ordering Information

Device	Package	Shipping
PJM3404NSA	SOT-23	3,000PCS/Reel&7inches



Conditions of Soldering and Storage

◆ Recommended condition of reflow soldering



Recommended peak temperature is over 245°C. If peak temperature is below 245°C, you may adjust the following parameters:

- Time length of peak temperature (longer)
- Time length of soldering (longer)
- Thickness of solder paste (thicker)

◆ Conditions of hand soldering

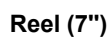
- Temperature: 300°C
- Time: 3s max.
- Times: one time

◆ Storage conditions

- **Temperature**
5 to 40°C
- **Humidity**
30 to 80% RH
- **Recommended period**
One year after manufacturing



- The method of packaging



Symbol	Value (unit: mm)
A	Ø 177.8±1
B	2.7±0.2
C	Ø 13.5±0.2
E	Ø 54.5±0.2
F	12.3±0.3
D	9.6+2/-0.3
T1	1.0±0.2
T2	1.2±0.2

